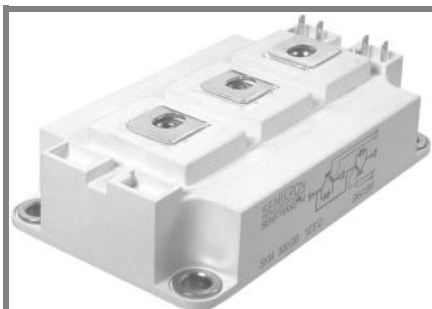


SKM 200GB12T4



SEMITRANS® 3

IGBT4 Modules

SKM 200GB12T4

Target Data

Features

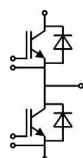
- IGBT4 = 4. Generation (Trench) IGBT
- V_{CEsat} with positive temperature coefficient
- High short circuit capability, self limiting to $6 \times I_{CNOM}$
- Soft switching 4. Generation CAL diode (CAL4)

Typical Applications

- AC inverter drives
- UPS
- Electronic welders at f_{sw} up to 20 kHz

Remarks

- Case temperature limited to $T_c = 125^\circ\text{C}$ max, recomm. $T_{op} = -40 \dots +150^\circ\text{C}$, product rel. results valid for $T_j \leq 150^\circ$

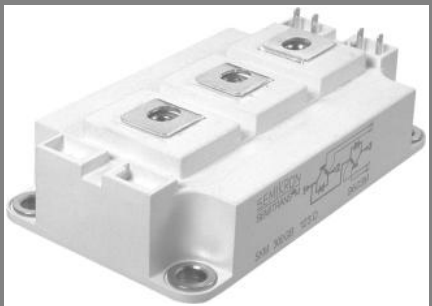


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Absolute Maximum Ratings			$T_c = 25\text{ }^{\circ}\text{C}$, unless otherwise specified	
Symbol	Conditions		Values	Units
IGBT				
V_{CES}	$T_j = 25\text{ }^{\circ}\text{C}$		1200	V
I_C	$T_j = 175\text{ }^{\circ}\text{C}$	$T_{case} = 25\text{ }^{\circ}\text{C}$	310	A
		$T_{case} = 80\text{ }^{\circ}\text{C}$	240	A
I_{CRM}	$I_{CRM} = 3 \times I_{CNOM}$		600	A
V_{GES}			± 20	V
t_{psc}	$V_{CC} = 600\text{ V}; V_{GE} \leq 15\text{ V}; T_j = 150\text{ }^{\circ}\text{C}$ $V_{CES} < 1200\text{ V}$		10	μs
Inverse Diode				
I_F	$T_j = 175\text{ }^{\circ}\text{C}$	$T_{case} = 25\text{ }^{\circ}\text{C}$	230	A
		$T_{case} = 80\text{ }^{\circ}\text{C}$	175	A
I_{FRM}	$I_{FRM} = 3 \times I_{FNOM}$		600	A
I_{FSM}	$t_p = 10\text{ ms}; \sin.$	$T_j = 175\text{ }^{\circ}\text{C}$	1100	A
Module				
$I_{t(RMS)}$			500	A
T_{vj}			-40 ... +175	$^{\circ}\text{C}$
T_{stg}			-40 ... +125	$^{\circ}\text{C}$
V_{isol}	AC, 1 min.		4000	V

Characteristics			T _c = 25 °C, unless otherwise specified				
Symbol	Conditions		min.	typ.	max.	Units	
IGBT							
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 8 mA		5	5,8	6,5	V	
I _{CES}	V _{GE} = 0 V, V _{CE} = V _{CES} T _j = 25 °C					mA	
V _{CE0}			T _j = 25 °C		0,8	0,9	V
			T _j = 150 °C		0,7	0,8	V
r _{CE}	V _{GE} = 15 V		T _j = 25°C		5	5,5	mΩ
			T _j = 150°C		7,5	8	mΩ
V _{CE(sat)}	I _{Cnom} = 200 A, V _{GE} = 15 V		T _j = 25°C _{chiplev.}		1,8	2	V
			T _j = 150°C _{chiplev.}		2,2	2,4	V
C _{ies}	V _{CE} = 25, V _{GE} = 0 V f = 1 MHz				12,4		nF
C _{oes}					0,82		nF
C _{res}					0,7		nF
Q _G	V _{GE} = -8V / +15V				1130		nC
R _{Gint}	T _j = 25 °C				3,75		Ω
t _{d(on)}	R _{Gon} = 1 Ω	V _{CC} = 600V I _{Cnom} = 200A T _j = 150 °C V _{GE} ≤ -8V	26			ns	
t _r						ns	
E _{on}	mJ						
t _{d(off)}	ns						
t _f	R _{Goff} = 1 Ω		19,5			ns	
E _{off}						mJ	
R _{th(j-c)}	per IGBT		0,14			K/W	

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GB

Characteristics							
Symbol	Conditions			min.	typ.	max.	Units
Inverse Diode							
V _F = V _{EC}	I _{Fnom} = 200 A; V _{GE} = 0 V	T _j = 25 °C _{chiplev.}		2,2	2,5		V
		T _j = 150 °C _{chiplev.}		2,1	2,45		V
V _{F0}		T _j = 25 °C		1,3	1,5		V
		T _j = 150 °C		0,9	1,1		V
r _F		T _j = 25 °C		4,5	5		mΩ
		T _j = 150 °C		6	6,75		mΩ
I _{RRM}	I _{Fnom} = 200 A	T _j = 150 °C		180			A
Q _{rr}	di/dt = 4700 A/μs			36			μC
E _{rr}	V _{GE} ≤ -8V			12,5			mJ
R _{th(j-c)}	per diode					0,26	K/W
Freewheeling Diode							
V _F = V _{EC}	I _{Fnom} = A; V _{GE} = V	T _j = °C _{chiplev.}					V
V _{F0}		T _j = °C					V
r _F		T _j = °C					V
I _{RRM}	I _{Fnom} = A	T _j = °C					A
Q _{rr}							μC
E _{rr}							mJ
	per diode						K/W
Module							
L _{CE}				15	20		nH
R _{CC'+EE'}	res., terminal-chip	T _{case} = 25 °C			0,35		mΩ
		T _{case} = 125 °C			0,5		mΩ
R _{th(c-s)}	per module			0,02	0,038		K/W
M _s	to heat sink M6			3	5		Nm
M _t	to terminals M6			2,5	5		Nm
w					325		g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.

